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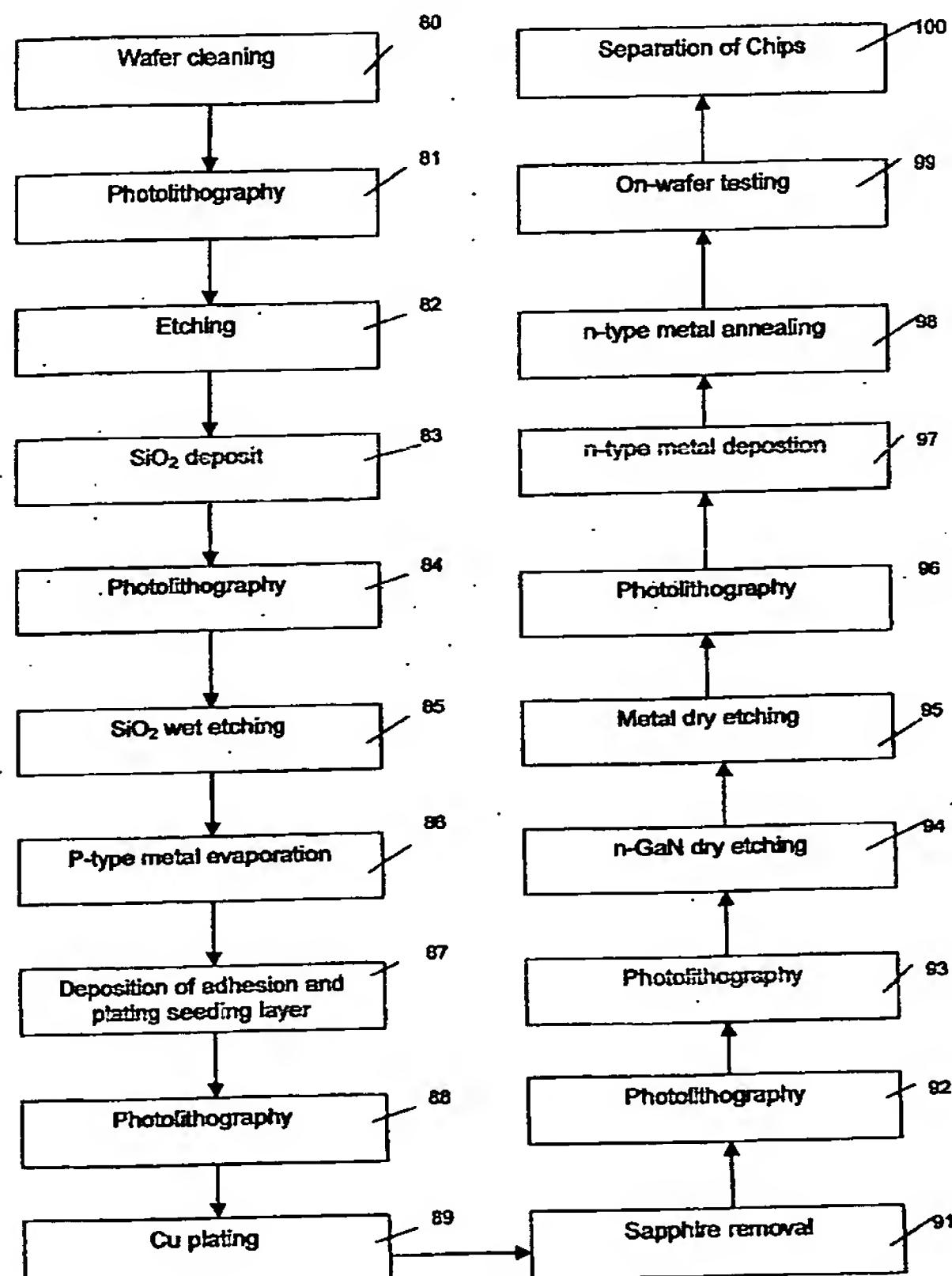
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**(54) Title: FABRICATION OF SEMICONDUCTOR DEVICES**



**(57) Abstract:** A method for fabrication of a semiconductor device on a substrate, the semiconductor having a wafer. The method includes the steps:(a) applying a seed layer of a thermally conductive metal to the wafer;(b) electroplating a relatively thick layer of the conductive metal on the seed layer; and(c) removing the substrate.A corresponding semiconductor device is also disclosed.



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